

ABSTRACT OF THE DISCLOSURE

A process gas containing any one of N_2 or N_2O is plasmanized and then a surface of a copper wiring layer is exposed to the plasmanized process gas, whereby a surface layer portion of a copper wiring layer is reformed and made into a copper diffusion preventing layer. According to this method, a noble semiconductor device can be provided, in which, along with increasing the operation speed, the copper diffusion is suppressed.

10

10021-959960